

MOS INTEGRATED CIRCUITS μ PD703037A, 703037AY, 70F3037A

V850/SB2[™] 32-BIT SINGLE-CHIP MICROCONTROLLERS

DESCRIPTION

The μ PD703037A, 703037AY, 70F3037A, and 70F3037AY (V850/SB2) are 32-bit single-chip microcontrollers of the V850 SeriesTM for AV equipment. 32-bit CPU, ROM, RAM, timer/counters, serial interfaces, A/D converter, DMA controller, and so on are integrated on a single chip.

The μ PD70F3037A and 70F3037AY have flash memory in place of the internal mask ROM of the μ PD703037A and 703037AY. Because flash memory allows the program to be written and erased electrically with the device mounted on the board, these products are ideal for the evaluation stages of system development, small-scale production, and rapid development of new products.

The μ PD703034A, 703034AY, 703035A, 703035AY, 70F3035A, and 70F3035AY products with a different ROM/RAM size are also available.

Detailed function descriptions are provided in the following user's manuals. Be sure to read them before designing.

V850/SB1[™], V850/SB2 User's Manual Hardware: U13850E V850 Series User's Manual Architecture: U10243E

FEATURES

- O Number of instructions: 74
- O Minimum instruction execution time: 76.9 ns (@ internal 13 MHz operation)
- O General-purpose registers: 32 bits × 32 registers
- Instruction set: Signed multiplication, saturation operations, 32-bit shift instructions, bit manipulation instructions, load/store instructions
- O Memory space: 16 MB linear address space
- O Internal memory ROM: 512 KB (μPD703037A, 703037AY: mask ROM)

512 KB (μPD70F3037A, 70F3037AY: flash memory)

RAM: 24 KB (μPD703037A, 703037AY, 70F3037A, 70F3037AY)

O Interrupt/exception: μ PD703037A, 70F3037A (external: 8, internal: 33 sources, exception: 1 source)

μPD703037AY, 70F3037AY (external: 8, internal: 34 sources, exception: 1 source)

- O I/O lines Total: 83
- O Timer/counters: 16-bit timer (2 channels: TM0, TM1)

8-bit timer (6 channels: TM2 to TM7)

Watch timer: 1 channel
 Watchdog timer: 1 channel
 IEBus[™] controller: 1 channel

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

- O Serial interface
 - Asynchronous serial interface (UART0, UART1)
 - Clocked serial interface (CSI0 to CSI3)
 - 3-wire variable length serial interface (CSI4)
 - l²C bus interface (l²C0, l²C1) (μPD703037AY, 70F3037AY only)
- O 10-bit resolution A/D converter: 12 channels
- O DMA controller: 6 channels
- O Real-time output port: 8 bits \times 1 channel or 4 bits \times 2 channels
- O ROM correction: 4 places can be corrected
- O Power-saving function: HALT/IDLE/STOP modes
- O Packages: 100-pin plastic QFP (14 × 20)
- Ο μΡD70F3037A, 70F3037AY
 - \bullet Can be replaced with μ PD703037A and 703037AY (internal mask ROM) in mass production

APPLICATIONS

O AV equipment (audio, car audio, VCR, TV, etc.)

ORDERING INFORMATION

	Part Number	Package	Internal ROM
	μPD703037AGF- xxx -3BA	100-pin plastic QFP (14 \times 20)	Mask ROM (512 KB)
	μ PD703037AYGF-xxx-3BA	100-pin plastic QFP (14 × 20)	Mask ROM (512 KB)
*	μ PD70F3037AGF-3BA	100-pin plastic QFP (14 × 20)	Flash memory (512 KB)
*	μ PD70F3037AYGF-3BA	100-pin plastic QFP (14 \times 20)	Flash memory (512 KB)

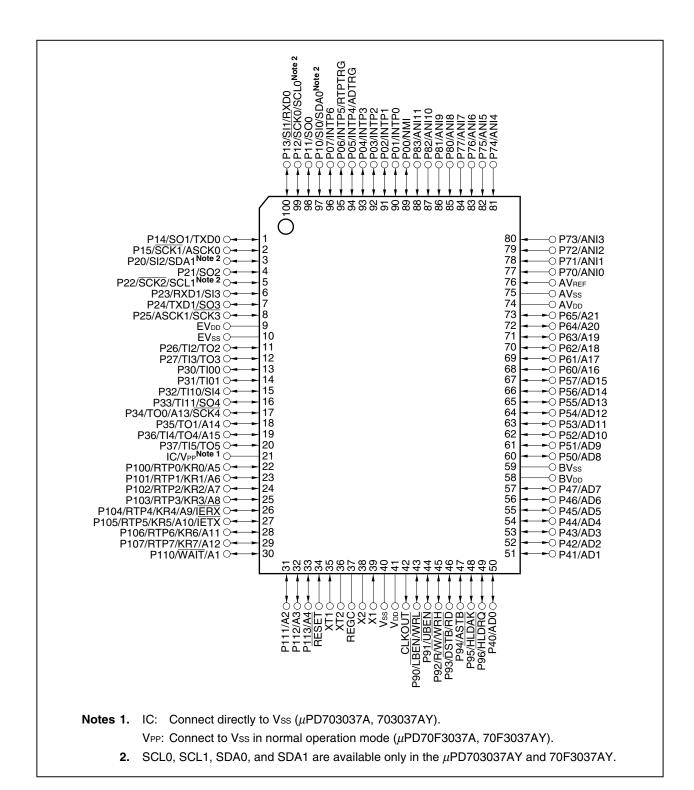
Remarks 1. xxx indicates ROM code suffix.

2. ROMless versions are not provided.

PIN CONFIGURATION (Top View)

100-pin plastic QFP (14 × 20)

- μPD703037AGF-××-3BA
- μPD703037AYGF-××-3BA
- μPD70F3037AGF-3BA
- μPD70F3037AYGF-3BA



Port 7

Port 8

Port 9

Port 10

PIN IDENTIFICATION

A1 to A21: Address Bus P70 to P77:

AD0 to AD15: Address/Data Bus P80 to P83:

ADTRG: A/D Trigger Input P90 to P96:

ANI0 to ANI11: Analog Input P100 to P107:

ASCK0, ASCK1: Asynchronous Serial Clock P110 to P113: Port 11

ASTB: Address Strobe RD: Read

AVDD: Analog Power Supply REGC: Regulator Control

AVREF: Analog Reference Voltage RESET: Reset

AVss: Analog Ground RTP0 to RTP7: Real-time Output Port
BVpb: Power Supply for Bus Interface RTPTRG: RTP Trigger Input
BVss: Ground for Bus Interface R/W: Read/Write Status
CLKOUT: PXD0_RXD1: Receive Data

CLKOUT: Clock Output RXD0, RXD1: Receive Data DSTB: Data Strobe SCK0 to SCK4: Serial Clock EV_{DD}: Power Supply for Port SCL0, SCL1: Serial Clock EVss: Ground for Port SDA0, SDA1: Serial Data HLDAK: Hold Acknowledge SI0 to SI4: Serial Input

HLDRQ: Hold Request SO0 to SO4: Serial Output IC: Internally Connected TI00, TI01, TI10, : Timer Input IERX: IEBus Receive Data TI11, TI2 to TI5

 IETX:
 IEBus Transmit Data
 TO0 to TO5:
 Timer Output

 INTP0 to INTP6:
 Interrupt Request from Peripherals
 TXD0, TXD1:
 Transmit Data

KR0 to KR7: Key Return UBEN: Upper Byte Enable

LBEN: Lower Byte Enable VDD: Power Supply

NMI: Non-Maskable Interrupt Request VPP: Programming Power Supply

P00 to P07: Port 0 Vss: Ground P10 to P15: Port 1 WAIT: Wait

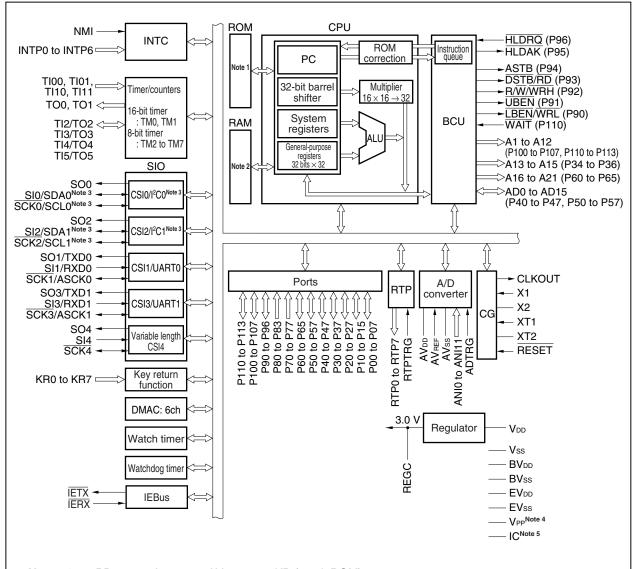
P20 to P27: Port 2 WRH: Write Strobe High Level Data
P30 to P37: Port 3 WRL: Write Strobe Low Level Data

P40 to P47: Port 4 X1, X2: Crystal for Main Clock P50 to P57: Port 5 XT1, XT2: Crystal for Sub-clock

P60 to P65: Port 6



INTERNAL BLOCK DIAGRAM



- Notes 1. μ PD703037A, 703037AY: 512 KB (mask ROM) μ PD70F3037A, 70F3037AY: 512 KB (flash memory)
 - **2.** μPD703037A, 703037AY, 70F3037A, 70F3037AY: 24 KB
 - 3. I²C bus interface and SDAn and SCLn pins (n = 0, 1) are available only in the μ PD703037AY and 70F3037AY.
 - **4.** μ PD70F3037A, 70F3037AY
 - **5.** μPD703037A, 703037AY



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1. DIFFERENCES AMONG PRODUCTS

Product Name	Incorporated	ROM	Л	RAM Size	Flash Memory	Package
	I ² C	Type	Size		Programming Pin	
μPD703034A	No	Mask ROM	128 KB	12 KB	No	100-pin QFP (14 × 20)
μPD703034AY	Yes					100-pin LQFP (14 × 14)
μPD703035A	No	Mask ROM	256 KB	16 KB	No	100-pin QFP (14 × 20)
μPD703035AY	Yes					100-pin LQFP (14 × 14)
μ PD70F3035A	No	Flash memory			Yes (VPP)	
μ PD70F3035AY	Yes					
μPD703037A	No	Mask ROM	512 KB	24 KB	No	100-pin QFP (14 × 20)
μPD703037AY	Yes					
μ PD70F3037A	No	Flash memory			Yes (VPP)	
μ PD70F3037AY	Yes					

- Cautions 1. There are differences in noise immunity and noise radiation between the flash memory and mask ROM versions. When pre-producing an application set with the flash memory version and then mass-producing it with the mask ROM version, be sure to conduct sufficient evaluations for the commercial samples (not engineering samples) of the mask ROM version.
 - 2. When replacing the flash memory versions with mask ROM versions, write the same code in the empty area of the internal ROM.



2. PIN FUNCTIONS

2.1 Port Pins

(1/2)

Pin Name	I/O	PULL	Function	Alternate Function	
P00	I/O	Yes	Port 0	NMI	
P01			8-bit I/O port	INTP0	
P02			Input/output can be specified in 1-bit units.	INTP1	
P03				INTP2	
P04				INTP3	
P05	1			INTP4/ADTRG	
P06				INTP5/RTPTRG	
P07				INTP6	
P10	I/O	Yes	Port 1	SI0/SDA0 ^{Note}	
P11			6-bit I/O port	SO0	
P12	1		Input/output can be specified in 1-bit units.	SCK0/SCL0 ^{Note}	
P13				SI1/RXD0	
P14				SO1/TXD0	
P15				SCK1/ASCK0	
P20	I/O	O Yes	Yes	Port 2	SI2/SDA1 ^{Note}
P21	1		8-bit I/O port	SO2	
P22			Input/output can be specified in 1-bit units.	SCK2/SCL1 ^{Note}	
P23				SI3/RXD1	
P24				SO3/TXD1	
P25					SCK3/ASCK1
P26		TI2/TO2			
P27				TI3/TO3	
P30	I/O	Yes	Port 3	TI00	
P31			8-bit I/O port	TI01	
P32		Input/output can be specified in 1-bit units.		TI10/SI4	
P33	1			TI11/SO4	
P34	1			TO0/A13/SCK4	
P35				TO1/A14	
P36				TI4/TO4/A15	
P37				TI5/TO5	
P40 to P47	I/O	No	Port 4 8-bit I/O port Input/output can be specified in 1-bit units.	AD0 to AD7	
P50 to P57	I/O	No	Port 5 8-bit I/O port Input/output can be specified in 1-bit units.	AD8 to AD15	

Note μ PD703037AY, 70F3037AY only.

(2/2)

Pin Name	I/O	PULL	Function	Alternate Function
P60 to P65	I/O	No	Port 6 6-bit I/O port Input/output can be specified in 1-bit units.	A16 to A21
P70 to P77	Input	No	Port 7 8-bit input port	ANI0 to ANI7
P80 to P83	Input	No	Port 8 4-bit input port	ANI8 to ANI11
P90	I/O	No	Port 9	LBEN/WRL
P91			7-bit I/O port	UBEN
P92			Input/output can be specified in 1-bit units.	R/W/WRH
P93				DSTB/RD
P94				ASTB
P95				HLDAK
P96				HLDRQ
P100	I/O	Yes	Port 10	RTP0/A5/KR0
P101			8-bit I/O port Input/output can be specified in 1-bit units.	RTP1/A6/KR1
P102			impul/output can be specified in 1-bit units.	RTP2/A7/KR2
P103				RTP3/A8/KR3
P104				RTP4/A9/KR4/IERX
P105				RTP5/A10/KR5/IETX
P106				RTP6/A11/KR6
P107				RTP7/A12/KR7
P110	I/O	Yes	Port 11	A1/WAIT
P111			4-bit I/O port	A2
P112			Input/output can be specified in 1-bit units.	А3
P113				A4



2.2 Non-Port Pins

(1/4)

Pin Name	I/O	PULL	Function	Alternate Function
A1	Output	Yes	Lower address bus used for external memory expansion	P110/WAIT
A2				P111
A3				P112
A4				P113
A5				P100/RTP0/KR0
A6				P101/RTP1/KR1
A7				P102/RTP2/KR2
A8				P103/RTP3/KR3
A9				P104/RTP4/KR4/IERX
A10				P105/RTP5/KR5/IETX
A11				P106/RTP6/KR6
A12				P107/RTP7/KR7
A13				P34/TO0/SCK4
A14				P35/TO1
A15				P36/TO4/TI4
A16 to A21	Output	No	Higher address bus used for external memory expansion	P60 to P65
AD0 to AD7	I/O	No	16-bit multiplexed address/data bus used for external memory	P40 to P47
AD8 to AD15			expansion	P50 to P57
ADTRG	Input	Yes	A/D converter external trigger input	P05/INTP4
ANI0 to ANI7	Input	No	Analog input to A/D converter	P70 to P77
ANI8 to ANI11				P80 to P83
ASCK0	Input	Yes	Baud rate clock input for UART0	P15/SCK1
ASCK1			Baud rate clock input for UART1	P25/SCK3
ASTB	Output	No	External address strobe output	P94
AV _{DD}	_	İ	Positive power supply for A/D converter and alternate port	_
AVREF	Input	-	Reference voltage input for A/D converter	_
AVss	_	1	Ground potential for A/D converter and alternate port	_
BV _{DD}	_	-	Positive power supply for bus interface and alternate port	_
BVss	-	-	Ground potential for bus interface and alternate port	_
CLKOUT	Output	_	Internal system clock output	_
DSTB	Output	No	External data strobe output	P93/RD
EV _{DD}	_	-	Positive power supply for I/O ports and alternate-function pins (except bus interface alternate port)	-
EVss	_	l	Ground potential for I/O ports and alternate-function pins (except bus interface alternate port)	-
HLDAK	Output	No	Bus hold acknowledge output	P95
HLDRQ	Input	No	Bus hold request input	P96
TILDING				

(2/4)

Pin Name	I/O	PULL	Function	Alternate Function
IERX	Input	Yes	IEBus data input	P104/RTP4/A9/KR4
ĪETX	Output		IEBus data output	P105/RTP5/A10/KR5
INTP0	Input	Yes	External interrupt request input (analog noise elimination)	P01
INTP1	1			P02
INTP2	1			P03
INTP3	1			P04
INTP4	Input	Yes	External interrupt request input (digital noise elimination)	P05/ADTRG
INTP5	1			P06/RTPTRG
INTP6	Input	Yes	External interrupt request input (digital noise elimination supporting remote controller)	P07
KR0	Input	Yes	Key return input	P100/RTP0/A5
KR1	1			P101/RTP1/A6
KR2				P102/RTP2/A7
KR3				P103/RTP3/A8
KR4	1			P104/RTP4/A9/IERX
KR5	1			P105/RTP5/A10/IETX
KR6	1			P106/RTP6/A11
KR7	1			P107/RTP7/A12
LBEN	Output	No	External data bus's lower byte enable output	P90/WRL
NMI	Input	Yes	Non-maskable interrupt request input	P00
RD	Output	No	Read strobe output	P93/DSTB
REGC	-	I	Regulator output stabilization capacitance connection	_
RESET	Input	-	System reset input	_
RTP0	Output	Yes	Real-time output port	P100/KR0/A5
RTP1				P101/KR1/A6
RTP2				P102/KR2/A7
RTP3				P103/KR3/A8
RTP4				P104/KR4/A9/IERX
RTP5				P105/KR5/A10/IETX
RTP6				P106/KR6/A11
RTP7				P107/KR7/A12
RTPTRG	Input	Yes	Real-time output port external trigger input	P06/INTP5
R/W	Output	No	External read/write status output	P92/WRH
RXD0	Input	Yes	Serial receive data input for UART0 and UART1	P13/SI1
RXD1				P23/SI3

(3/4)

Pin Name	I/O	PULL	Function	(3/4) Alternate Function
SCK0	I/O	Yes	Serial clock I/O (3-wire type) for CSI0 to CSI3	P12/SCL0 ^{Note}
SCK1				P15/ASCK0
SCK2				P22/SCL1 ^{Note}
SCK3				P25/ASCK1
SCK4	I/O	Yes	Serial clock I/O (3-wire type) for variable length CSI4	P34/TO0/A13
SCL0	I/O	Yes	Serial clock I/O for I ² C0 and I ² C1	P12/SCK0
SCL1			(μPD703037AY, 70F3037AY only)	P22/SCK2
SDA0	I/O	Yes	Serial transmit/receive data I/O for I ² C0 and I ² C1	P10/SI0
SDA1			(μPD703037AY, 70F3037AY only)	P20/SI2
SI0	Input	Yes	Serial receive data input (3-wire type) for CSI0 to CSI3	P10/SDA0 ^{Note}
SI1				P13/RXD0
SI2				P20/SDA1 ^{Note}
SI3				P23/RXD1
SI4	Input	Yes	Serial receive data input (3-wire type) for variable length CSI4	P32/TI10
SO0	Output	Yes	Serial transmit data output (3-wire type) for CSI0 to CSI3	P11
SO1				P14/TXD0
SO2				P21
SO3				P24/TXD1
SO4	Output	Yes	Serial transmit data output (3-wire type) for variable length CSI4	P33/TI11
TI00	Input	Yes	External count clock input for TM0/external capture trigger input for TM0	P30
TI01			External capture trigger input for TM0	P31
TI10			External count clock input for TM1/external capture trigger input for TM1	P32/SI4
TI11			External capture trigger input for TM1	P33/SO4
TI2	Input	Yes	External count clock input for TM2 to TM5	P26/TO2
TI3				P27/TO3
TI4				P36/TO4/A15
TI5				P37/TO5
TO0	Output	Yes	Pulse signal output for TM0 and TM1	P34/A13/SCK4
TO1				P35/A14
TO2	Output	Yes	Pulse signal output for TM2 to TM5	P26/TI2
ТО3				P27/TI3
TO4				P36/TI4/A15
TO5				P37/TI5
TXD0	Output	Yes	Serial transmit data output for UART0 and UART1	P14/SO1
TXD1				P24/SO3
UBEN	Output	No	Higher byte enable output for external data bus	P91
V_{DD}	_	_	Positive power supply pin	_

Note μ PD703037AY, 70F3037AY only.

(4/4)

Pin Name	I/O	PULL	Function	Alternate Function
V _{PP}	-	-	High voltage apply pin for program write/verify (μPD70F3037A, 70F3037AY only)	-
Vss	_	_	Ground potential	-
WAIT	Input	Yes	Control signal input for inserting wait in bus cycle	P110/A1
WRH	Output	No	Higher byte write strobe signal output for external data bus	P92/R/W
WRL	Output	No	Lower byte write strobe signal output for external data bus	P90/LBEN
X1	Input	No	Resonator connection for main clock	-
X2	_			-
XT1	Input	No	Resonator connection for subsystem clock	-
XT2	_			_



2.3 Pin I/O Circuits and Recommended Connection of Unused Pins

The input/output circuit type of each pin and recommended connection of unused pins are show in Table 2-1. For the input/output schematic circuit diagram of each type, refer to Figure 2-1.

Table 2-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (1/2)

Pin	Alternate Function	I/O Circuit Type	I/O Buffer Power Supply	Recommended Connection of Unused Pins
P00	NMI	8-A	EV _{DD}	Input state: Independently connect to EVDD or
P01	INTP0			EVss via a resistor.
P02	INTP1			Output state: Leave open.
P03	INTP2			
P04	INTP3			
P05	INTP4/ADTRG			
P06	INTP5/RTPTRG			
P07	INTP6			
P10	SI0/SDA0	10-A	EV _{DD}	Input state: Independently connect to EV _{DD} or
P11	SO0	26]	EVss via a resistor.
P12	SCK0/SCL0	10-A]	Output state: Leave open.
P13	SI1/RXD0	8-A]	
P14	SO1/TXD0	26]	
P15	SCK1/ASCK0	10-A]	
P20	SI2/SDA1	10-A	EV _{DD}	Input state: Independently connect to EV _{DD} or
P21	SO2	26]	EVss via a resistor. Output state: Leave open.
P22	SCK2/SCL1	10-A]	Output state. Leave open.
P23	SI3/RXD1	8-A]	
P24	SO3/TXD1	26]	
P25	SCK3/ASCK1	10-A		
P26	TI2/TO2	8-A		
P27	TI3/TO3			
P30	TI00	8-A	EV _{DD}	Input state: Independently connect to EV _{DD} or
P31	TI01			EVss via a resistor. Output state: Leave open.
P32	TI10/SI4			Output State. Leave open.
P33	TI11/SO4			
P34	TO0/A13/SCK4			
P35	TO1/A14	5-A		
P36	TI4/TO4/A15	8-A		
P37	TI5/TO5			
P40 to P47	AD0 to AD7	5	BV _{DD}	Input state: Independently connect to BVDD or BVss via a resistor.
P50 to P57	AD8 to AD15	5	BV _{DD}	Output state: Leave open.
P60 to P65	A16 to A21	5	BV _{DD}	

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Table 2-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (2/2)

Pin	Alternate Function	I/O Circuit Type	I/O Buffer Power Supply	Recommended Connection of Unused Pins
P70 to P77	ANI0 to ANI7	9	AV _{DD}	Independently connect to AVDD or AVss via a resistor.
P80 to P83	ANI8 to ANI11	9	AV _{DD}	
P90	LBEN/WRL	5	BV _{DD}	Input state: Independently connect to BVDD or
P91	UBEN			BVss via a resistor. Output state: Leave open.
P92	R/W/WRH			Output state. Leave open.
P93	DSTB/RD			
P94	ASTB			
P95	HLDAK			
P96	HLDRQ			
P100	RTP0/A5/KR0	10-A	EV _{DD}	Input state: Independently connect to EVDD or
P101	RTP1/A6/KR1			EVss via a resistor. Output state: Leave open.
P102	RTP2/A7/KR2			Output state. Leave open.
P103	RTP3/A8/KR3			
P104	RTP4/A9/KR4/IERX			
P105	RTP5/A10/KR5/IETX			
P106	RTP6/A11/KR6			
P107	RTP7/A12/KR7			
P110	A1/WAIT	5-A	EV _{DD}	Input state: Independently connect to EVDD or
P111	A2			EVss via a resistor. Output state: Leave open.
P112	A3			Output state. Leave open.
P113	A4			
CLKOUT	-	4	BV _{DD}	Leave open.
RESET	-	2	EV _{DD}	-
XT1	-	16	-	Connect to Vss via a resistor.
XT2	-	16	-	Leave open.
AVREF	-	-	-	Connect to AVss via a resistor.
IC ^{Note 1}	-	-	-	Connect directly to Vss.
VPP ^{Note 2}	_	_	_	Connect to Vss.

Notes 1. μPD703037A, 703037AY

2. μ PD70F3037A, 70F3037AY

Caution Three power supply systems are available to supply power to the I/O buffers of the V850/SB2's pins: EVDD, BVDD, and AVDD. The voltage ranges that can be used for these I/O buffer power supplies are shown below.

EV_{DD}, BV_{DD}: 3.0 to 5.5 V AV_{DD}: 4.5 to 5.5 V

The electrical specifications differ depending on whether the power supply voltage range is 3.0 to under 4.0 V, or 4.0 to 5.5 V.

Type 5-A Type 2 Pull-up enable $V_{\text{DD}} \\$ Data IN O O IN/OUT Output disable Schmitt-triggered input with hysteresis characteristics Input enable Type 4 Type 8-A Pull-up Data enable $V_{\text{DD}} \\$ OUT Data Output O IN/OUT disable Output disable Push-pull output that can be set for high-impedance output (both P-ch and N-ch off) Type 5 Type 9 V_{DD} Data Comparator IN O-O IN/OUT Output disable VREF (threshold voltage) Input enable Input enable

Figure 2-1. Pin Input/Output Circuits (1/2)

Caution VDD in the circuit diagrams can be read as EVDD, BVDD, or AVDD, as appropriate.

Type 10-A Type 26 Pull-up Pull-up enable enable **V**DD V_{DD} Data Data P-ch O IN/OUT O IN/OUT Open drain Open drain Output disable - N-ch Output disable Type 16 Feedback cutoff XT1 XT2

Figure 2-1. Pin Input/Output Circuits (2/2)

Caution \mbox{Vdd} in the circuit diagrams can be read as \mbox{EVdd} , \mbox{BVdd} , or \mbox{AVdd} , as appropriate.



3. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings ($T_A = 25$ °C, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V _{DD}	V _{DD} pin	-0.5 to +7.0	V
*	V _{PP}	V _{PP} pin (μPD70F3037A, 70F3037AY only)	-0.5 to +8.5	V
	AV _{DD}	AV _{DD} pin	-0.5 to +7.0	V
	BV _{DD}	BV _{DD} pin	-0.5 to +7.0	V
	EV _{DD}	EV _{DD} pin	-0.5 to +7.0	V
	AVss	AVss pin	-0.5 to +0.5	V
	BVss	BVss pin	-0.5 to +0.5	V
	EVss	EVss pin	-0.5 to +0.5	V
Input voltage	V _{I1}	Note 1 (BVpp pin)	-0.5 to BV _{DD} + 0.5 ^{Note 4}	V
	V _{I2}	Note 2, RESET (EVDD pin)	-0.5 to EV _{DD} + 0.5 ^{Note 4}	V
Analog input voltage	VIAN	Note 3 (AV _{DD} pin)	-0.5 to AV _{DD} + 0.5 ^{Note 4}	V
Analog reference input voltage	AVREF	AV _{REF} pin	-0.5 to AV _{DD} + 0.5 ^{Note 4}	V
Output current, low	lol	Per pin	4.0	mA
		Total for P00 to P07, P10 to P15, P20 to P25	25	mA
		Total for P26, P27, P30 to P37, P100 to P107, P110 to P113	25	mA
		Total for P40 to P47, P90 to P96, CLKOUT	25	mA
		Total for P50 to P57, P60 to P65	25	to +8.5 V to +7.0 V to +7.0 V to +7.0 V to +7.0 V to +0.5 V to +0.5 V VDD + 0.5 Note 4 V VDD + 0.5 Note 4 V VDD + 0.5 Note 4 V 4.0 MA 25 MA 25 MA 25 MA -4.0 MA -25 MA -26 MA -27 MA -28 MA -29 MA -29 MA -20 MA -20 MA -21 MA -22 MA -25 MA -25 MA -25 MA -26 MA -27 MA -28 MA -29 MA -29 MA -20 MA -20 MA -21 MA -22 MA -25 MA -25 MA -26 MA -27 MA -28 MA -29 MA -29 MA -20 MA
Output current, high	Іон	Per pin	-4.0	mA
		Total for P00 to P07, P10 to P15, P20 to P25	-25	mA
		Total for P26, P27, P30 to P37, P100 to P107, P110 to P113	-25	mA
		Total for P40 to P47, P90 to P96, CLKOUT	-25	mA
		Total for P50 to P57, P60 to P65	-25	mA
Output voltage	V 01	Note 1, CLKOUT (BVpp pin)	-0.5 to BV _{DD} + 0.5 ^{Note 4}	V
*	V ₀₂	Note 2 (EV _{DD} pin)	-0.5 to EV _{DD} + 0.5 ^{Note 4}	V
Operating ambient temperature	TA	Normal operation mode	-40 to +85	°C
*		Flash memory programming mode (µPD70F3037A, 70F3037AY only)	-20 to +85	°C
Storage temperature	T _{stg}	μPD703037A, 703037AY	-65 to +150	°C
		μPD70F3037A, 70F3037AY	-40 to +125	°C

Notes 1. Ports 4, 5, 6, 9, and their alternate-function pins

- 2. Ports 0, 1, 2, 3, 10, 11, and their alternate-function pins
- 3. Ports 7, 8, and their alternate-function pins
- 4. Be sure not to exceed the absolute maximum ratings (MAX. value) of each supply voltage.

Cautions 1. Do not directly connect the output (or I/O) pins of IC products to each other, or to VDD, VCC, and GND. Open-drain pins or open-collector pins, however, can be directly connected to each other. Direct connection of the output pins between an IC product and an external circuit is possible, if the output pins can be set to the high-impedance state and the output timing of the external circuit is designed to avoid output conflict.

2. Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

The ratings and conditions indicated for DC characteristics and AC characteristics represent the quality assurance range during normal operation.

Capacitance (TA = 25 °C, VDD = AVDD = BVDD = EVDD = VSS = AVSS = BVSS = EVSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Сі	fc = 1 MHz			15	pF
I/O capacitance	Сю	Unmeasured pins returned to 0 V			15	pF
Output capacitance	Со				15	pF

Operating Conditions

★ (1) Operating frequency

Operat	ing Frequency (fxx)	V _{DD}	AV _{DD}		BV _{DD}	EV _{DD}	Remark
			Note 1	Note 2			
2 to 13 MHz		4.0 to 5.5 V	4.5 to 5.5 V	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	Note 3
32.768 kHz	Other than IDLE mode	4.0 to 5.5 V	4.5 to 5.5 V	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	-
	IDLE mode	3.5 to 5.5 V	-	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	Note 4

Notes 1. When A/D converter is used

- 2. When A/D converter is not used
- 3. During STOP mode (when only watch timer is operating), V_{DD} = 3.5 to 5.5 V. Shifting to STOP mode or restoring from STOP mode must be performed at V_{DD} = 4.0 V min.
- **4.** Shifting to IDLE mode or restoring from IDLE mode must be performed at $V_{DD} = 4.0 \text{ V}$ min.

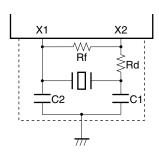
(2) CPU operating frequency

Parameter	Symbol	Conditions		TYP.	MAX.	Unit
CPU operating frequency	fcpu	Main clock operation	0.25		13	MHz
		Subclock operation		32.768		kHz



Recommended Oscillator

- (1) Main clock oscillator ($T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C}$)
 - (a) Connection of ceramic resonator or crystal resonator



Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Oscillation frequency	fxx		2		13	MHz
Oscillation stabilization time	ı	Upon reset release		2 ¹⁹ /fxx		S
	ı	Upon STOP mode release		Note		S

Note The TYP. value differs depending on the setting of the oscillation stabilization time select register (OSTS).

- Cautions 1. The main clock oscillator operates on the output voltage of the on-chip regulator (3.0 V). External clock input is prohibited.
 - 2. When using the main clock oscillator, wire as follows in the area enclosed by the broken lines in the above figure to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - . Always make the ground point of the oscillator capacitor the same potential as Vss.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - Do not fetch signals from the oscillator.
 - 3. Ensure that the duty of oscillation waveform is between 5.5 and 4.5.
 - 4. Sufficiently evaluate the matching between the μ PD703037A, 703037AY, 70F3037A, 70F3037AY and the resonator.

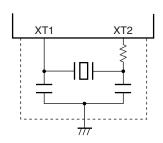
\star (b) Ceramic resonator (T_A = -40 to +85 °C)

Manufacturer	Part Number	Oscillation Frequency	Rec	ommended	Circuit Cons	stant	Oscillation Voltage Range		
		fxx (MHz)	C1 (pF)	C2 (pF)	Rf (kΩ)	Rd (k Ω)	MIN. (V)	MAX. (V)	
Murata Mfg.	CSTLS6M29G53-B0	6.290	On-chip	On-chip	1	0	4.0	5.5	
Co., Ltd.	CSTCR6M29G53-R0		On-chip	On-chip	-	0	4.0	5.5	
	CSTLA12M5T55001-B0	12.583	On-chip	On-chip	-	0	4.0	5.5	
	CSTCV12M5T54J01-R0		On-chip	On-chip	_	0	4.0	5.5	

Caution The oscillator constant and oscillation voltage range indicate conditions of stable oscillation.

Oscillation frequency precision is not guaranteed. For applications requiring oscillation frequency precision, the oscillation frequency must be adjusted on the implementation circuit. For details, please contact directly the manufacturer of the resonator you will use.

- (2) Subclock oscillator ($T_A = -40 \text{ to } +85 \text{ }^{\circ}\text{C}$)
 - (a) Connection of crystal resonator



Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Oscillation frequency	fхт		32	32.768	35	kHz
Oscillation stabilization time	-			10		S

- Cautions 1. The subclock oscillator operates on the output voltage of the on-chip regulator (3.0 V). External clock input is prohibited.
 - 2. When using the subclock oscillator, wire as follows in the area enclosed by the broken lines in the above figure to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - Always make the ground point of the oscillator capacitor the same potential as Vss.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - Do not fetch signals from the oscillator.
 - 3. Sufficiently evaluate the matching between the μ PD703037A, 703037AY, 70F3037A, 70F3037AY and the resonator.



DC Characteristics ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $AV_{DD} = 4.5 \text{ to } 5.5 \text{ V}$ (when A/D converter is used), $AV_{DD} = 4.0 \text{ to } 5.5 \text{ V}$ (when A/D converter is not used), $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Co	Conditions		TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Note 1	$4.0 \text{ V} \leq BV_{DD} \leq 5.5 \text{ V}$	0.7BV _{DD}		BV _{DD}	V
			3.0 V ≤ BV _{DD} < 4.0 V	0.8BV _{DD}		BV _{DD}	٧
	V _{IH2}	Note 2	4.0 V ≤ EV _{DD} ≤ 5.5 V	0.7EV _{DD}		EV _{DD}	٧
			3.0 V ≤ EV _{DD} < 4.0 V	0.8EV _{DD}		EV _{DD}	V
	VIH3	Note 3, RESET	4.0 V ≤ EV _{DD} ≤ 5.5 V	0.7EV _{DD}		EV _{DD}	V
			3.0 V ≤ EV _{DD} < 4.0 V	0.8EV _{DD}		EV _{DD}	V
	V _{IH4}	Note 4		0.7AV _{DD}		AV _{DD}	V
Input voltage, low	V _{IL1}	Note 1		BVss		0.3BV _{DD}	V
	V _{IL2}	Note 2		EVss		0.3EV _{DD}	V
	V _{IL3}	Note 3, RESET		EVss		0.3EV _{DD}	V
	V _{IL4}	Note 4		AVss		0.3AV _{DD}	٧
Output voltage, high	V _{OH1}	Note 1, CLKOUT	$3.0 \text{ V} \le \text{BV}_{\text{DD}} \le 5.5 \text{ V},$ Iон = $-100 \ \mu\text{A}$	BV _{DD} - 0.5			٧
			$4.0 \text{ V} \le \text{BV}_{DD} \le 5.5 \text{ V},$ Iон = -3 mA	BV _{DD} - 1.0			V
	V _{OH2}	Notes 2, 3	$3.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ $\text{Ioh} = -100 \ \mu\text{A}$	EV _{DD} - 0.5			V
			$4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ $\text{Ioh} = -3 \text{ mA}$	EV _{DD} - 1.0			V
Output voltage, low	Vol	IoL = 3 mA, 3.0 V ≤ BVDD, EVD	D ≤ 5.5 V			0.5	٧
		IoL = 3 mA, 4.0 V ≤ BVDD, EVD	D ≤ 5.5 V			0.4	V
V _{PP} power supply voltage	V _{PP1}	Normal operation		0		0.54	V
Input leakage current, high	Іпн	$V_{I} = V_{DD} = BV_{DD} = I$	EV _{DD} = AV _{DD}			5	μΑ
Input leakage current, low	ILIL	V1 = 0 V				- 5	μΑ
Output leakage current, high	Ісон	Vo = Vdd = BVdd =	EV _{DD} = AV _{DD}			5	μΑ
Output leakage current, low	ILOL	Vo = 0 V				- 5	μΑ

Notes 1. Ports 4, 5, 6, 9, and their alternate-function pins

- 2. P11, P14, P21, P24, P34, P35, P110 to P113, and their alternate-function pins
- **3.** P00 to P07, P10, P12, P13, P15, P20, P22, P23, P25 to P27, P30 to P33, P36, P37, P100 to P107, and their alternate-function pins
- 4. Ports 7, 8, and their alternate-function pins



DC Characteristics ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $AV_{DD} = 4.5 \text{ to } 5.5 \text{ V}$ (when A/D converter is used), $AV_{DD} = 4.0 \text{ to } 5.5 \text{ V}$ (when A/D converter is not used), $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$) (2/2)

Para	ameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Supply current	μPD703037A,	I _{DD1}	In normal of	peration mode ^{Note 1}		15	25	mA
	μPD703037AY	I _{DD2}	In HALT mo	In HALT mode ^{Note 1} In IDLE Watch timer operating mode ^{Note 2}		6	13	mA
		Іррз				1	4	mA
		I _{DD4}	In STOP mode	Watch timer, subclock oscillator operating		13	70	μΑ
				Subclock oscillator stopped, XT1 = Vss		8	70	μΑ
		IDD5	In normal op operation) [№]	peration mode (subclock		50	150	μΑ
		I _{DD6}	In IDLE mod	de (subclock operation)Note 3		13	70	μΑ
	μPD70F3037A,	I _{DD1}	In normal of	peration mode ^{Note 1}		30	58	mA
	μPD70F3037AY	I _{DD2}	In HALT mo	ode ^{Note 1}		9	20	mA
		Іррз	In IDLE mode ^{Note 2}	Watch timer operating		1	4	mA
		IDD4	In STOP mode	Watch timer, subclock oscillator operating		13	100	μΑ
				Subclock oscillator stopped, XT1 = Vss		8	100	μΑ
		I _{DD5}		In normal operation mode (subclock operation) ^{Note 3}		300	900	μΑ
_		I _{DD6}	In IDLE mod	de (subclock operation) ^{Note 3}		170	340	μΑ
Pull-up resistand	ce	RL	VIN = 0 V		10	30	100	kΩ

Notes 1. $f_{CPU} = f_{XX} = 13 \text{ MHz}$, all peripheral functions operating

- **2.** fxx = 13 MHz
- **3.** $f_{CPU} = f_{XT} = 32.768 \text{ kHz}$, main clock oscillator stopped

Remark TYP. values are reference values for when $T_A = 25$ °C, $V_{DD} = BV_{DD} = EV_{DD} = AV_{DD} = 5.0$ V. The current consumed by the output buffer is not included.

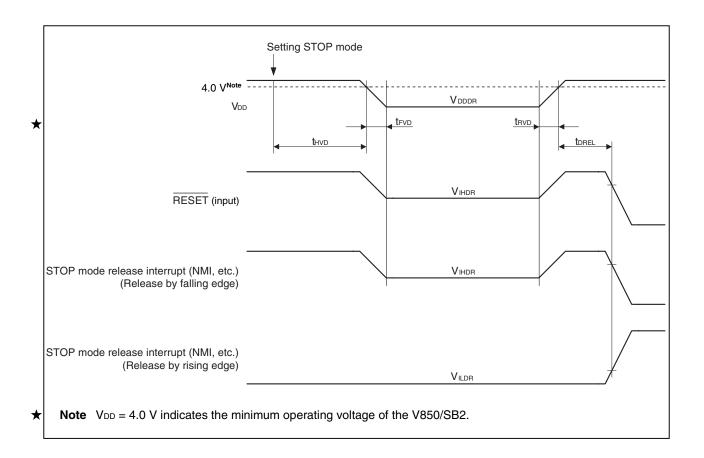


Data Retention Characteristics (TA = -40 to +85 °C, Vss = AVss = BVss = EVss = 0 V)

	Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
*	Data retention voltage	VDDDR	STOP mode (all functions not operating)		2.7 ^{Note}		5.5	V
	Data retention current	IDDDR	$V_{DD} = V_{DDDR}, \mu PD703037A, \ XT1 = V_{SS} \mu PD703037AY$			8	70	μΑ
			(Subclock stopped)	μPD70F3037A, μPD70F3037AY		8	100	μΑ
	Power supply voltage rise time	trvd			200			μs
	Power supply voltage fall time	t FVD			200			μs
	Power supply voltage hold time (from STOP mode setting)	thvd			0			ms
	STOP mode release signal input time	torel			0			ms
I	Data retention high-level input voltage	VIHDR	All input ports		0.9VDDDR		VDDDR	V
	Data retention low-level input voltage	VILDR	All input ports		0		0.1VDDDR	٧

Note During STOP mode (when only watch timer is operating), $V_{DD} = 3.5$ to 5.5 V. Shifting to STOP mode or restoring from STOP mode must be performed at $V_{DD} = 4.0$ V min.

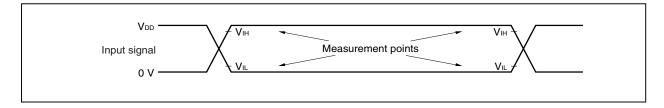
Remark TYP. values are reference values for when $T_A = 25$ °C.



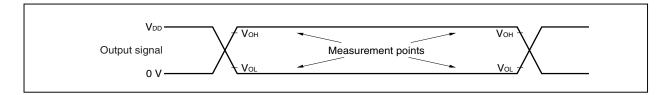


AC Characteristics (TA = -40 to +85 °C, VDD = 4.0 to 5.5 V, BVDD = EVDD = 3.0 to 5.5 V, AVDD = 4.5 to 5.5 V (when A/D converter is used), AVDD = 4.0 to 5.5 V (when A/D converter is not used), Vss = AVss = BVss = EVss = 0 V)

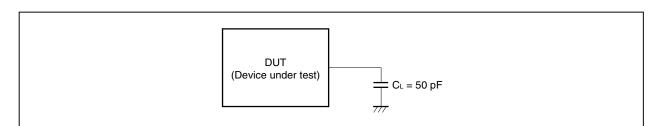
AC Test Input Test Point (VDD: EVDD, BVDD, AVDD)



AC Test Output Test Points (VDD: EVDD, BVDD)



Load Conditions



Caution If the load capacitance exceeds 50 pF due to the circuit configuration, bring the load capacitance of the device to 50 pF or less by inserting a buffer or by some other means.



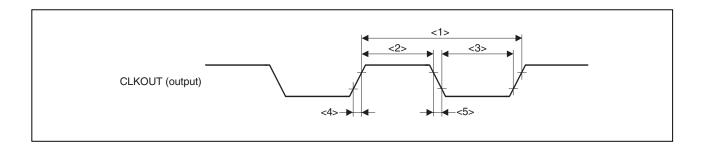
(1) Clock timing

(a) $T_A = -40$ to +85 °C, $V_{DD} = BV_{DD} = 4.0$ to 5.5 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
CLKOUT output cycle	<1>	tсүк		76.9 ns	31.2 μs	
CLKOUT high-level width	<2>	twкн		0.4tcyк – 12		ns
CLKOUT low-level width	<3>	twkl		0.4tcyк – 12		ns
CLKOUT rise time	<4>	tĸĸ			12	ns
CLKOUT fall time	<5>	t KF			12	ns

(b) $T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $BV_{DD} = 3.0 \text{ to } 4.0 \text{ V}$, $EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
CLKOUT output cycle	<1>	t cyk		76.9 ns	31.2 <i>μ</i> s	
CLKOUT high-level width	<2>	twкн		0.4tcyк – 15		ns
CLKOUT low-level width	<3>	twkl		0.4tсүк – 15		ns
CLKOUT rise time	<4>	tkr			15	ns
CLKOUT fall time	<5>	t KF			15	ns

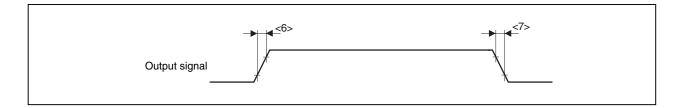




(2) Output waveform (other than port 4, port 5, port 6, port 9, and CLKOUT)

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

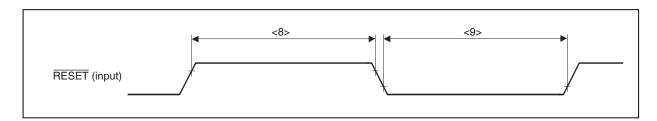
Parameter	Sym	nbol	Conditions	MIN.	MAX.	Unit
Output rise time	<6>	tor			20	ns
Output fall time	<7>	tof			20	ns



(3) Reset timing

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
RESET pin high-level width	<8>	twrsh		500		ns
RESET pin low-level width	<9>	twrsl		500		ns





(4) Bus timing

(a) Clock asynchronous ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = BV_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$)

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
Address setup time (to ASTB↓)	<10>	tsast		0.5T – 16		ns
Address hold time (from ASTB↓)	<11>	thsta		0.5T – 15		ns
Address float delay time from DSTB↓	<12>	t fda			0	ns
Data input setup time from address	<13>	tsaid			(2 + n)T - 40	ns
Data input setup time from DSTB↓	<14>	tsdid			(1 + n)T – 40	ns
Delay time from ASTB↓ to DSTB ↓	<15>	tosto		0.5T – 15		ns
Data input hold time (from DSTB↑)	<16>	thdid		0		ns
Address output time from DSTB ↑	<17>	t dda		(1 + i)T – 15		ns
Delay time from DSTB↑ to ASTB↑	<18>	tddst1		0.5T – 15		ns
Delay time from DSTB ↑ to ASTB↓	<19>	tddst2		(1.5 + i)T - 15		ns
DSTB low-level width	<20>	twdl		(1 + n)T – 22		ns
ASTB high-level width	<21>	twsтн		T – 15		ns
Data output time from DSTB ↓	<22>	todod			10	ns
Data output setup time (to DSTB↑)	<23>	tsodd		(1 + n)T – 25		ns
Data output hold time (from DSTB↑)	<24>	thdod		T – 20		ns
WAIT setup time (to address)	<25>	tsawt1	n ≥ 1		1.5T – 40	ns
	<26>	tsawt2	n ≥ 1		(1.5 + n)T – 40	ns
WAIT hold time (from address)	<27>	thawt1	n ≥ 1	(0.5 + n)T		ns
	<28>	thawt2	n ≥ 1	(1.5 + n)T		ns
WAIT setup time (to ASTB↓)	<29>	tsstwt1	n ≥ 1		T – 32	ns
	<30>	tsstwt2	n ≥ 1		(1 + n)T – 32	ns
WAIT hold time (from ASTB↓)	<31>	thstwt1	n ≥ 1	nT		ns
	<32>	thstwt2	n ≥ 1	(1 + n)T		ns
HLDRQ high-level width	<33>	twнqн		T + 10		ns
HLDAK low-level width	<34>	twhal		T – 15		ns
Bus output delay time from HLDAK↑	<35>	t DHAC		-6		ns
Delay time from $\overline{HLDRQ} \downarrow$ to $\overline{HLDAK} \downarrow$	<36>	tdhqha1			(2n + 7.5)T + 25	ns
Delay time from HLDRQ↑ to HLDAK↑	<37>	tdhqha2		0.5T	1.5T + 25	ns

Remarks 1. T = 1/fcpu (fcpu: CPU operating clock frequency)

n: Number of wait clocks inserted in the bus cycle.
 The sampling timing changes when a programmable wait is inserted.

- 3. i: Number of idle states inserted after a read cycle (0 or 1).
- **4.** The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.



(b) Clock asynchronous ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $BV_{DD} = 3.0 \text{ to } 4.0 \text{ V}$, $EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$)

Parameter	Syr	nbol	Conditions	MIN.	MAX.	Unit
Address setup time (to ASTB↓)	<10>	tsast		0.5T - 20		ns
Address hold time (from ASTB↓)	<11>	t HSTA		0.5T - 22		ns
Address float delay time from DSTB↓	<12>	t FDA			0	ns
Data input setup time from address	<13>	tsaid			(2 + n)T - 50	ns
Data input setup time from DSTB↓	<14>	tsdid			(1 + n)T – 50	ns
Delay time from ASTB↓ to DSTB ↓	<15>	tosto		0.5T – 15		ns
Data input hold time (from DSTB↑)	<16>	thdid		0		ns
Address output time from DSTB ↑	<17>	t dda		(1 + i)T – 15		ns
Delay time from DSTB↑ to ASTB↑	<18>	tDDST1		0.5T - 15		ns
Delay time from DSTB ↑ to ASTB↓	<19>	tddst2		(1.5 + i)T - 15		ns
DSTB low-level width	<20>	twdl		(1 + n)T – 35		ns
ASTB high-level width	<21>	twsтн		T – 15		ns
Data output time from DSTB ↓	<22>	todod			10	ns
Data output setup time (to DSTB↑)	<23>	tsodd		(1 + n)T – 35		ns
Data output hold time (from DSTB ↑)	<24>	thdod		T – 25		ns
WAIT setup time (to address)	<25>	tsawt1	n ≥ 1		1.5T – 55	ns
	<26>	tsawt2	n ≥ 1		(1.5 + n)T - 55	ns
WAIT hold time (from address)	<27>	thawt1	n ≥ 1	(0.5 + n)T		ns
	<28>	thawt2	n ≥ 1	(1.5 + n)T		ns
WAIT setup time (to ASTB↓)	<29>	tsstwt1	n ≥ 1		T – 45	ns
	<30>	tsstwt2	n ≥ 1		(1 + n)T – 45	ns
WAIT hold time (from ASTB↓)	<31>	t _{HSTWT1}	n ≥ 1	nT		ns
	<32>	thstwt2	n ≥ 1	(1 + n)T		ns
HLDRQ high-level width	<33>	twнqн		T + 10		ns
HLDAK low-level width	<34>	twhal		T – 25		ns
Bus output delay time from HLDAK↑	<35>	t DHAC		-6		ns
Delay time from HLDRQ↓ to HLDAK↓	<36>	tdhqha1			(2n + 7.5)T + 25	ns
Delay time from HLDRQ↑ to HLDAK↑	<37>	tdhqha2		0.5T	1.5T + 25	ns

Remarks 1. T = 1/fcpu (fcpu: CPU operating clock frequency)

- n: Number of wait clocks inserted in the bus cycle.
 The sampling timing changes when a programmable wait is inserted.
- 3. i: Number of idle states inserted after a read cycle (0 or 1).
- **4.** The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.



(c) Clock synchronous (TA = -40 to +85 °C, VDD = BVDD = 4.0 to 5.5 V, EVDD = 3.0 to 5.5 V, Vss = AVss = BVss = EVss = 0 V)

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<38>	t dka		0	19	ns
Delay time from CLKOUT↑ to address float	<39>	tfka		-12	10	ns
Delay time from CLKOUT↓ to ASTB	<40>	t DKST		0	19	ns
Delay time from CLKOUT↑ to DSTB	<41>	t DKD		0	19	ns
Data input setup time (to CLKOUT↑)	<42>	tsidk		20		ns
Data input hold time (from CLKOUT↑)	<43>	thkid		5		ns
Data output delay time from CLKOUT↑	<44>	tokod			19	ns
WAIT setup time (to CLKOUT↓)	<45>	tswтк		20		ns
WAIT hold time (from CLKOUT↓)	<46>	tнкwт		5		ns
HLDRQ setup time (to CLKOUT↓)	<47>	tsнак		20		ns
HLDRQ hold time (from CLKOUT↓)	<48>	tнкна		5		ns
Delay time from CLKOUT↑ to address float (during bus hold)	<49>	t DKF			19	ns
Delay time from CLKOUT↑ to HLDAK	<50>	t DKHA			19	ns

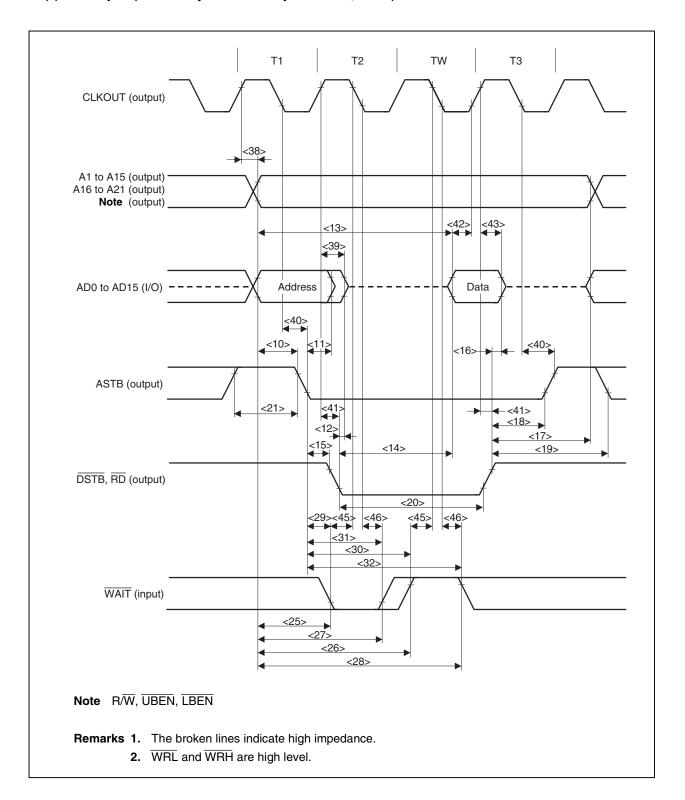
Remark The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(d) Clock synchronous (TA = -40 to +85 °C, VDD = 4.0 to 5.5 V, BVDD = 3.0 to 4.0 V, EVDD = 3.0 to 5.5 V, Vss = AVss = BVss = EVss = 0 V)

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<38>	t dka		0	22	ns
Delay time from CLKOUT↑ to address float	<39>	tfka		-16	10	ns
Delay time from CLKOUT↓ to ASTB	<40>	t DKST		0	19	ns
Delay time from CLKOUT↑ to DSTB	<41>	t DKD		0	22	ns
Data input setup time (to CLKOUT↑)	<42>	t sidk		20		ns
Data input hold time (from CLKOUT [↑])	<43>	thkid		5		ns
Data output delay time from CLKOUT↑	<44>	t DKOD			22	ns
WAIT setup time (to CLKOUT↓)	<45>	tswтк		24		ns
WAIT hold time (from CLKOUT↓)	<46>	tнкwт		5		ns
HLDRQ setup time (to CLKOUT↓)	<47>	t shqk		24		ns
HLDRQ hold time (from CLKOUT↓)	<48>	tнкна		5		ns
Delay time from CLKOUT [↑] to address float (during bus hold)	<49>	t DKF			19	ns
Delay time from CLKOUT↑ to HLDAK	<50>	t DKHA			19	ns

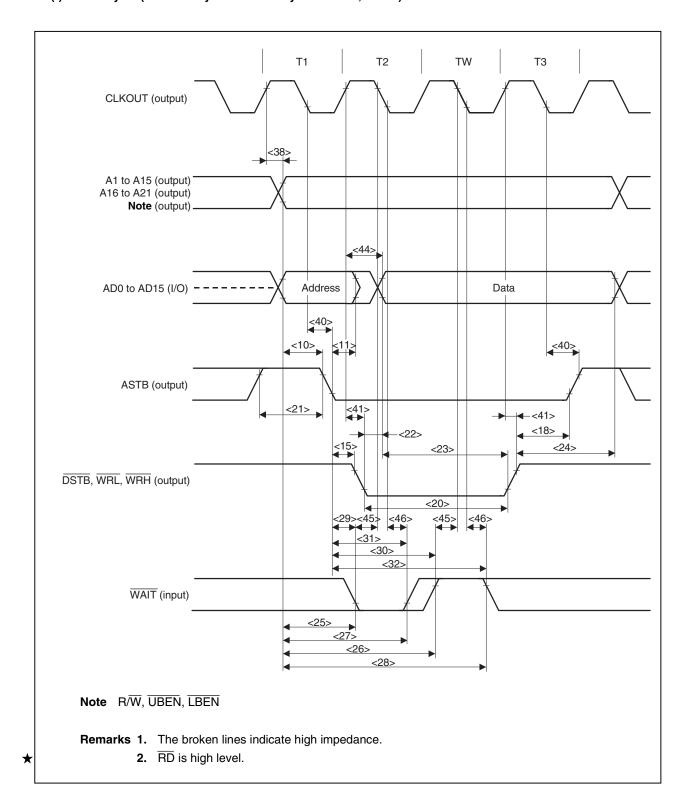
Remark The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(e) Read cycle (CLKOUT synchronous/asynchronous, 1 wait)



⋆

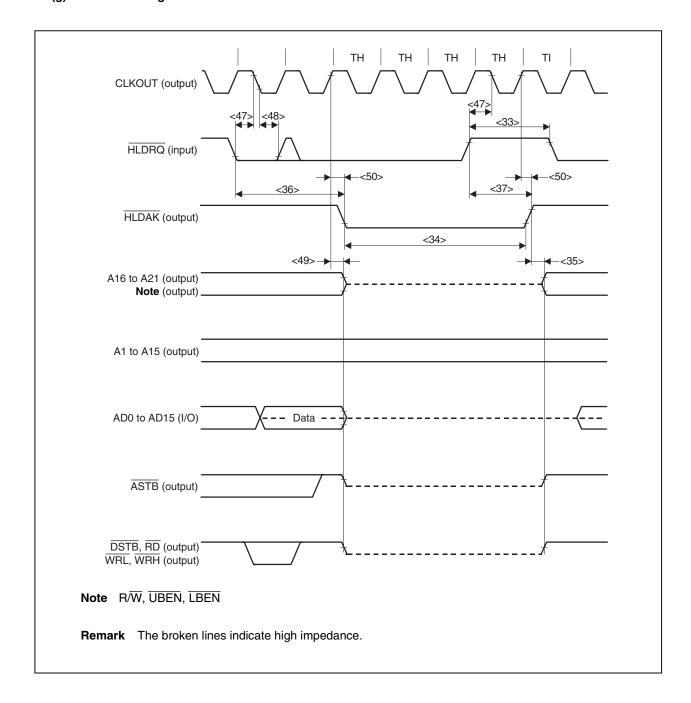
(f) Write cycle (CLKOUT synchronous/asynchronous, 1 wait)



32



(g) Bus hold timing





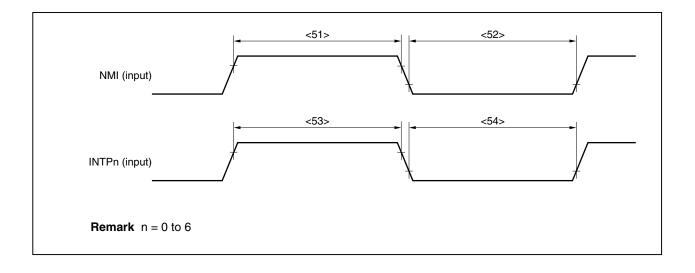
(5) Interrupt timing

(Ta = -40 to +85 °C, VdD = 4.0 to 5.5 V, BVdD = EVdD = 3.0 to 5.5 V, Vss = AVss = BVss = EVss = 0 V)

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
NMI high-level width	<51>	twnih		500		ns
NMI low-level width	<52>	twnil		500		ns
INTPn high-level width	<53>	twiтн	n = 0 to 3, analog noise elimination	500		ns
			n = 4, 5, digital noise elimination	3T + 20		ns
			n = 6, digital noise elimination	3Tsmp + 20		ns
INTPn low-level width	<54>	t wiTL	n = 0 to 3, analog noise elimination	500		ns
			n = 4, 5, digital noise elimination	3T + 20		ns
			n = 6, digital noise elimination	3Tsmp + 20		ns

Remarks 1. T = 1/fxx

2. Tsmp = Noise elimination sampling clock cycle





(6) RPU timing

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Tln0, Tln1 high-level width	<55>	tтıнп	n = 0, 1	2T _{sam} + 20 ^{Note}		ns
TIn0, TIn1 low-level width	<56>	t TILn	n = 0, 1	2T _{sam} + 20 ^{Note}		ns
TIm high-level width	<57>	tтıнт	m = 2 to 5	3T + 20		ns
TIm low-level width	<58>	t⊤ı∟m	m = 2 to 5	3T + 20		ns

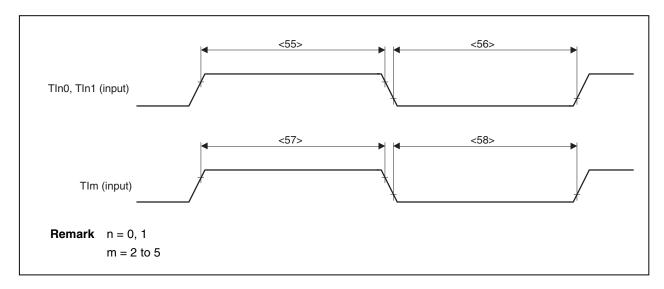
Note T_{sam} can select the following count clocks by setting the PRMn2 to PRMn0 bits of prescaler mode registers n0, n1 (PRMn0, PRMn1).

When n = 0 (TM0), $T_{sam} = 2T$, 4T, 16T, 64T, 256T, or 1/INTWTNI cycle

When n = 1 (TM1), $T_{sam} = 2T$, 4T, 16T, 32T, 128T, or 256T

However, when the Tln0 valid edge is selected as the count clock, Tsam = 4T.

Remark T = 1/fxx

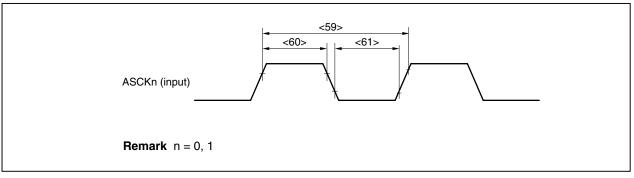


(7) Asynchronous serial interface (UART0, UART1) timing

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Syn	nbol	Conditions	MIN.	MAX.	Unit
ASCKn cycle time	<59>	t KCY13		200		ns
ASCKn high-level width	<60>	t кн13		80		ns
ASCKn low-level width	<61>	t KL13		80		ns

Remark n = 0, 1





(8) 3-wire serial interface (CSI0 to CSI3) timing

(a) Master mode

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
SCKn cycle	<62>	tkcy1		400		ns
SCKn high-level width	<63>	t _{KH1}		140		ns
SCKn low-level width	<64>	t _{KL1}		140		ns
SIn setup time (to SCKn↑)	<65>	tsıĸı		50		ns
SIn hold time (from SCKn↑)	<66>	t ksıı		50		ns
Delay time from SCKn↓ to SOn output	<67>	tkso1			60	ns

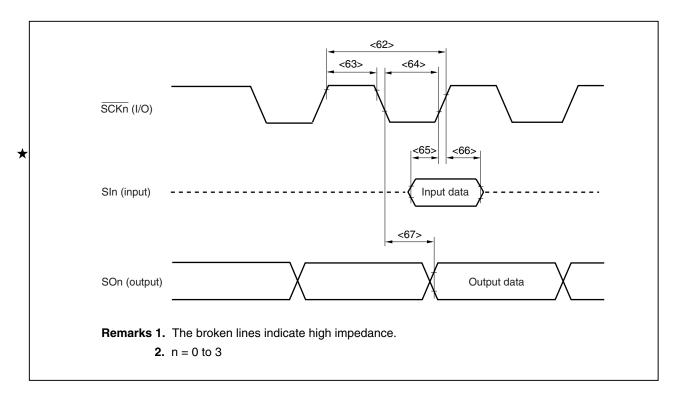
Remark n = 0 to 3

(b) Slave mode

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
SCKn cycle	<62>	tkcy2		400		ns
SCKn high-level width	<63>	t _{KH2}		140		ns
SCKn low-level width	<64>	tĸL2		140		ns
SIn setup time (to SCKn↑)	<65>	tsık2		50		ns
SIn hold time (from SCKn↑)	<66>	tksi2		50		ns
Delay time from SCKn↓ to SOn output	<67>	tkso2	4.0 V ≤ EV _{DD} ≤ 5.5 V		70	ns
			3.0 V ≤ EV _{DD} < 4.0 V		100	ns

Remark n = 0 to 3





(9) 3-wire variable length serial interface (CSI4) timing

(a) Master mode

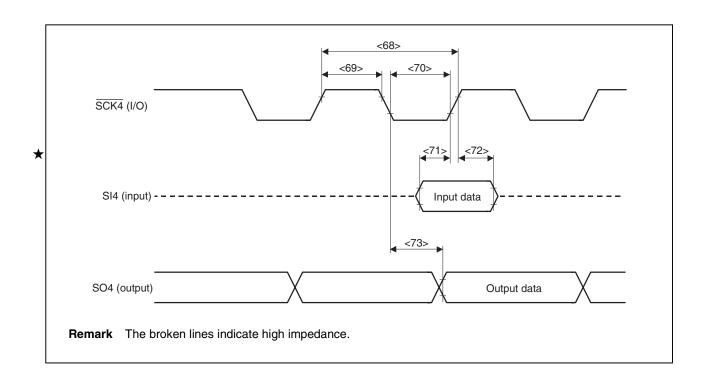
 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Sy	mbol	Conditions	MIN.	MAX.	Unit
SCK4 cycle	<68>	tkcy1	$4.0~V \leq EV_{DD} \leq 5.5~V$	200		ns
			$3.0~\text{V} \leq \text{EV}_{\text{DD}} < 4.0~\text{V}$	400		ns
SCK4 high-level width	<69>	t ĸн1	$4.0~V \leq EV_{DD} \leq 5.5~V$	60		ns
			$3.0~\text{V} \leq \text{EV}_{\text{DD}} < 4.0~\text{V}$	140		ns
SCK4 low-level width	<70>	t _{KL1}	$4.0~V \leq EV_{DD} \leq 5.5~V$	60		ns
			$3.0~\text{V} \leq \text{EV}_{\text{DD}} < 4.0~\text{V}$	140		ns
SI4 setup time (to SCK4↑)	<71>	tsıĸı	$4.0~V \leq EV_{DD} \leq 5.5~V$	25		ns
			$3.0 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$	50		ns
SI4 hold time (from SCK4↑)	<72>	t KSI1		20		ns
Delay time from SCK4↓ to SO4 output	<73>	tkso1			55	ns

(b) Slave mode

 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parameter	Sy	mbol	Conditions	MIN.	MAX.	Unit
SCK4 cycle	<68>	tkcy2	$4.0~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$	200		ns
			$3.0 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}$	400		ns
SCK4 high-level width	<69>	t _{KH2}	$4.0~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$	60		ns
			$3.0 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$	140		ns
SCK4 low-level width	<70>	t _{KL2}	$4.0~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$	60		ns
			$3.0 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}$	140		ns
SI4 setup time (to SCK4↑)	<71>	tsık2	$4.0~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$	25		ns
			$3.0 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}$	50		ns
SI4 hold time (from SCK4↑)	<72>	tksi2		20		ns
Delay time from SCK4↓ to SO4	<73>	tkso2	$4.0~\text{V} \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V}$		55	ns
output			$3.0 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}$		100	ns



(10) I^2C bus mode (μ PD703037AY, 70F3037AY only)

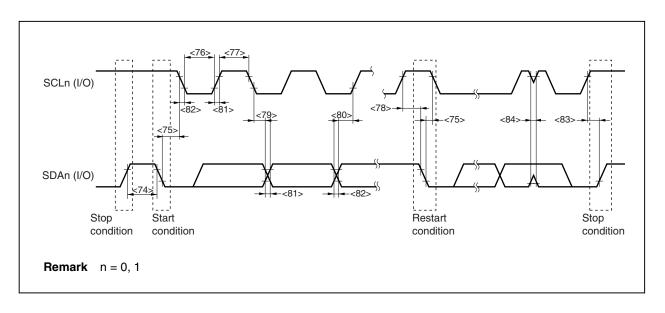
 $(T_A = -40 \text{ to } +85 \text{ °C}, V_{DD} = 4.0 \text{ to } 5.5 \text{ V}, BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V})$

Parai	meter	Syr	nbol	Norma	al Mode	High-Spe	ed Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCLn clock fre	equency	_	fclk	0	100	0	400	kHz
Bus-free time stop/start cond	•	<74>	tbuf	4.7	_	1.3	-	μs
Hold time ^{Note 1}		<75>	thd:sta	4.0	-	0.6	-	μs
SCLn clock lov	w-level width	<76>	tLOW	4.7	-	1.3	-	μs
SCLn clock hig	gh-level width	<77>	thigh	4.0	-	0.6	-	μs
Setup time for conditions	start/restart	<78>	tsu:sta	4.7	_	0.6	-	μs
Data hold time	CBUS compatible master	<79>	thd:dat	5.0	_	_	-	μѕ
	I ² C mode			O ^{Note 2}	-	O ^{Note 2}	0.9 ^{Note 3}	μs
Data setup tim	ne	<80>	tsu:dat	250	_	100 ^{Note 4}	-	ns
SDAn and SC time	Ln signal rise	<81>	tR	-	1000	20 + 0.1Cb ^{Note 5}	300	ns
SDAn and SC time	Ln signal fall	<82>	tF	-	300	20 + 0.1Cb ^{Note 5}	300	ns
Stop condition	setup time	<83>	tsu:sto	4.0	-	0.6	_	μs
Pulse width of suppressed by	•	<84>	tsp	-	_	0	50	ns
Capacitance lo	oad of each	_	Cb	-	400	-	400	pF

Notes 1. At the start condition, the first clock pulse is generated after the hold time.

- 2. The system requires a minimum of 300 ns hold time internally for the SDAn signal (at VIHmin. of SCLn signal) in order to occupy the undefined area at the falling edge of SCLn.
- 3. If the system does not extend the SCLn signal's low-level width (tLow), only the maximum data hold time (thd:dat) needs to be satisfied.
- **4.** The high-speed mode I²C bus can be used in the normal-mode I²C bus system. In this case, set the high-speed mode I²C bus so that it meets the following conditions.
 - If the system does not extend the SCLn signal's low-level width: $t_{SU:DAT} \ge 250 \text{ ns}$
 - If the system extends the SCLn signal's low-level width:
 Transmit the following data bit to the SDAn line prior to the SCLn line release (transmit + tsu:DAT = 1,000 + 250 = 1,250 ns: Normal mode l²C bus specification).
- **5.** Cb: Total capacitance of one bus line (unit: pF)

Remark n = 0, 1



A/D Converter Characteristics (TA = -40 to +85 °C, VDD = AVDD = AVREF = 4.5 to 5.5 V, Vss = AVss = 0 V, Output pin load capacitance: CL = 50 pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	_		10	10	10	bit
Overall error ^{Note 1}	_	ADM2 = 00H			±0.6	%FSR
		ADM2 = 01H			±1.0	%FSR
Conversion time	tconv		5		10	μs
Zero-scale error ^{Note 1}	_				±0.4	%FSR
Full-scale error Note 1	_	ADM2 = 00H			±0.4	%FSR
		ADM2 = 01H			±0.6	%FSR
Integral linearity error Note 2	_	ADM2 = 00H			±4.0	LSB
		ADM2 = 01H			±6.0	LSB
Differential linearity error Note 2	_	ADM2 = 00H			±4.0	LSB
		ADM2 = 01H			±6.0	LSB
Analog reference voltage	AVREF	AVREF = AVDD	4.5		5.5	٧
Analog power supply voltage	AVDD		4.5		5.5	>
Analog input voltage	VIAN		AVss		AVREF	٧
AV _{REF} input current	AIREF			1	2	mA
AV _{DD} power supply current	Aldd	ADM2 = 00H		3	6	mA
		ADM2 = 01H		4	8	mA

Notes 1. Excluding quantization error (±0.05 %FSR)

2. Excluding quantization error (±0.5 LSB)

Remarks 1. LSB: Least Significant Bit FSR: Full Scale Range

2. ADM2: A/D converter mode register 2



IEBus Controller Characteristics ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$, $BV_{DD} = EV_{DD} = 3.0 \text{ to } 5.5 \text{ V}$, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
IEBus system clock	fs	Communication mode: fixed to		6.0 ^{Note 1}		MHz
frequency		mode 1		6.29 Notes 1, 2		MHz

Notes 1. 6.0 MHz and 6.29 MHz can not be used together for the IEBus system clock frequency

2. Although the system clock frequency specified in the IEBus specification is 6.0 MHz, operation is guaranteed at 6.29-MHz system clock in the V850/SB2.

Regulator (TA = -40 to +85 °C, VDD = 4.0 to 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output stabilization time	treg	Stabilization capacitance C = 1 μ F (Connected to REGC pin)	1			ms

- Cautions 1. Be sure to start inputting supply voltage V_{DD} when $\overline{RESET} = V_{SS} = EV_{SS} = BV_{SS} = 0 \text{ V}$ (the above state), and make \overline{RESET} high level after the tree period has elapsed.
 - 2. If supply voltage BV_{DD} or EV_{DD} is input before the tree period has elapsed following the input of supply voltage V_{DD}, note that data may be driven from the pins until the tree period has elapsed because the I/O buffers' power supply was turned on while the circuit was in an undefined state.



★3.1 Flash Memory Programming Mode (µPD70F3037A, 70F3037AY only)

Write/erase characteristics (TA = -20 to +85 °C, $V_{DD} = AV_{DD} = BV_{DD} = EV_{DD} = 4.5$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 \text{ V}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VPP power supply voltage	V _{PP2}	During flash memory programming	7.5	7.8	8.1	V
V _{DD} power supply current	IDD	When VPP = VPP2, fxx = 13 MHz			61	mA
VPP power supply current	Ірр	VPP = VPP2			100	mA
Step erase time	ter	Note 1		0.2		S
Overall erase time per area	tera	When the step erase time = 0.2 s, Note 2			20	s/area
Write-back time	twв	Note 3		1		ms
Number of write-backs per write-back command	Сwв	When the write-back time = 1 ms, Note 4			300	Count/write- back command
Number of erase/write-backs	CERWB				16	Count
Step writing time	twn	Note 5		20		μs
Overall writing time per word	twrw	When the step writing time = 20 μ s (1 word = 4 bytes), Note 6	20		200	μs/word
Number of rewrites per area	CERWR	1 erase + 1 write after erase = 1 rewrite, Note 7		100		Count/area

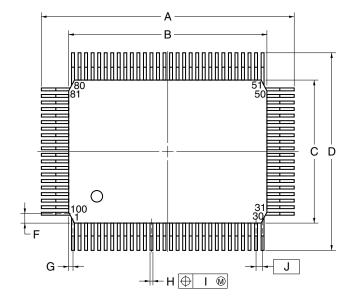
- Notes 1. The recommended setting value of the step erase time is 0.2 s.
 - 2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.
 - 3. The recommended setting value of the write-back time is 1 ms.
 - **4.** Write-back is executed once by the issuance of the write-back command. Therefore, the retry count must be the maximum value minus the number of commands issued.
 - **5.** The recommended setting value of the step writing time is 20 μ s.
 - **6.** 20 μ s is added to the actual writing time per word. The internal verify time during and after the writing is not included.
 - **7.** When writing initially to shipped products, it is counted as one rewrite for both "erase to write" and "write only".

```
Example (P: Write, E: Erase) Shipped product \longrightarrow P \rightarrow E \rightarrow P \rightarrow E \rightarrow P: 3 rewrites Shipped product \rightarrow E \rightarrow P \rightarrow E \rightarrow P \rightarrow E \rightarrow P: 3 rewrites
```

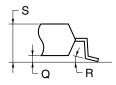
- **Remarks 1.** When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.
 - 2. Area 0 = 000000H to 01FFFFH Area 2 = 040000H to 05FFFFH Area 1 = 020000H to 03FFFFH Area 3 = 060000H to 07FFFFH

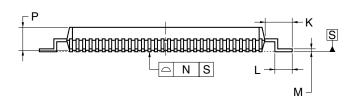
4. PACKAGE DRAWING

100-PIN PLASTIC QFP (14x20)



detail of lead end





NOTE

Each lead centerline is located within 0.15 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	23.6±0.4
В	20.0±0.2
С	14.0±0.2
D	17.6±0.4
F	0.8
G	0.6
Н	0.30±0.10
1	0.15
J	0.65 (T.P.)
K	1.8±0.2
L	0.8±0.2
М	$0.15^{+0.10}_{-0.05}$
N	0.10
P	2.7±0.1
Q	0.1±0.1
R	5°±5°
S	3.0 MAX.

P100GF-65-3BA1-4

5. RECOMMENDED SOLDERING CONDITIONS

The μ PD703037A, 703037AY, 70F3037A, and 70F3037AY should be soldered and mounted under the following recommended conditions.

For the details of the recommended soldering conditions, refer to the document **Semiconductor Device Mounting Technology Manual (C10535E).**

For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Table 5-1. Surface Mounting Type Soldering Conditions (1/2)

(1) μ PD703037AGF-xxx-3BA: 100-pin plastic QFP (14 × 20) μ PD703037AYGF-xxx-3BA: 100-pin plastic QFP (14 × 20)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235 °C, Time: 30 seconds max. (at 210 °C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	IR35-207-2
VPS	Package peak temperature: 215 °C, Time: 25 to 40 seconds (at 200 °C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	VP15-207-2
Wave soldering	Solder bath temperature: 260 °C max., Time: 10 seconds max., Count: Once Preheating temperature: 120 °C max. (package surface temperature) Exposure limit: 7 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	WS60-207-1
Partial heating	Pin temperature: 300 °C max., Time: 3 seconds max. (per pin row)	

Note After opening the dry pack, store it at 25 °C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Table 5-1. Surface Mounting Type Soldering Conditions (2/2)

(2) μ PD70F3037AGF-3BA: 100-pin plastic QFP (14 × 20) μ PD70F3037AYGF-3BA: 100-pin plastic QFP (14 × 20)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235 °C, Time: 30 seconds max. (at 210 °C or higher), Count: Two times or less Exposure limit: 3 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	IR35-203-2
VPS	Package peak temperature: 215 °C, Time: 25 to 40 seconds. (at 200 °C or higher), Count: Two times or less Exposure limit: 3 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	VP15-203-2
Wave soldering	Solder bath temperature: 260 °C max., Time: 10 seconds max., Count: once Preheating temperature: 120 °C max. (package surface temperature) Exposure limit: 3 days ^{Note} (after that, prebake at 125 °C for 20 to 72 hours)	WS60-203-1
Partial heating	Pin temperature: 300 °C max., Time: 3 seconds max. (per pin row)	-

Note After opening the dry pack, store it at 25 °C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

*APPENDIX NOTES ON TARGET SYSTEM DESIGN

The following shows a diagram of the connection conditions between the in-circuit emulator option board and conversion connector. Design your system making allowances for conditions such as the form of parts mounted on the target system as shown below.

Side view In-circuit emulator IE-703002-MC In-circuit emulator option board IE-703037-MC-EM1 Conversion connector NEXB-100-SD/RB YQGUIDE YQPACK100RB NQPACK100RB Target system Note YQSOCKET100SDN (included with IE-703002-MC) to this portion for adjusting the height (height: 3.2 mm). Top view IE-703002-MC Target system NEXB-100-SD/RB Pin 1 position IE-703037-MC-EM1 YQPACK100RB, NQPACK100RB, YQGUIDE Connection condition diagram IE-703037-MC-EM1 Connect to IE-703002-MC Pin 1 position NEXB-100-SD/RB YQPACK100RB NQPACK100RB 33.2 mm Target system 20 mm

Appendix-1. 100-pin Plastic QFP (14 × 20)

NOTES FOR CMOS DEVICES -

(1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

(3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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Related document μ PD703034A, 703034AY, 703035A, 703035AY, 70F3035A, 70F3035AY Data Sheet (U14780E)

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